

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent application of :
Min Kim et al. : **BOX NEW APPLICATIONS**
Serial No. (new) :
Filed November 8, 2001 :

TRENCH ISOLATION STRUCTURE HAVING A CURVILINEAR INTERFACE AT UPPER
CORNERS OF THE TRENCH ISOLATION REGION, AND METHOD OF MANUFACTURING THE
SAME

PRELIMINARY AMENDMENT

Honorable Commissioner For Patents
Washington, D.C. 20131

Sir:

Prior to the examination of the above-identified application, the following
amendments and remarks are submitted:

In the Specification¹

Kindly amend the paragraph [0100] to read as follows:

[0100] FIG. 6 shows a first embodiment of trench isolation structure in which a
trench 116 extends into a semiconductor substrate 104 from an upper surface of the
substrate, and a trench isolation layer occupies the trench to electrically isolate active

¹ A copy of any revised paragraphs/sections of the specification showing additions and deletions
thereto is attached as ATTACHMENT "A".

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